

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re DIVISIONAL application of )  
Shunpei YAMAZAKI et al. )  
Based on Serial No. 10/214,691 ) Group Art Unit: 2826  
Filed: August 9, 2002 ) Examiner: Abraham  
For: SEMICONDUCTOR DEVICE AND )  
METHOD OF FABRICATING SAME )

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 10/214,691 and predecessor Application Serial No. 08/785,486 and copies of the references can be found in those applications.

Respectfully submitted,

  
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Substitute for form 1449A/PTO				<i>Complete if Known</i>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	1	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
		5,686,328		Zhang et al.	11/11/97	
		5,763,899		Yamazaki et al.	06/09/98	
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		6,207,969 B1		Yamazaki et al.	03/27/01	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T <sup>2</sup>
		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.			
		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995			

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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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		5,811,327		Funai et al.	09/22/98	
		5,818,076		Zhang et al.	10/06/98	
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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
		JP	07-335900		Teramoto Satoshi	12/22/95	Abst.
		JP	64-081324			03/27/89	Abst.

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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		IBM Technical Disclosure Bulletin, Vol. 11, No.7, A.R. Baker, Jr.	

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Sheet	8	of	12	Attorney Docket Number	0756-7218

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		5,712,191		Nakajima et al.	01/27/98	
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		5,550,070		Funai et al.	08/27/96	
		5,693,959		Inoue et al.	12/02/97	

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		Wolf, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Chapter 4, page 274 (1990).	

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